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CONTENTS

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BRIEF REPORTS

Electronic structure: wide-band, narrow-band, and strongly correlated systems

- Theoretical investigation of the phases of the organic insulator $(\text{TMTTF})_2\text{PF}_6$ 4541
D. Schmeltzer and A. R. Bishop
- Transmission properties of light through the Fibonacci-class multilayers 4545
Xiangbo Yang, Youyan Liu, and Xiujun Fu
- Electronic and magnetic states in doped LaCoO_3 4549
K. Tsutsui, J. Inoue, and S. Maekawa
- Exactly solvable site-dependent Hubbard model 4553
Feng Pan and J. P. Draayer
- Anisotropy of thermal expansion and electronic topological transitions in Zn and Cd under pressure 4557
D. L. Novikov, M. I. Katsnelson, A. V. Trefilov, A. J. Freeman, N. E. Christensen, A. Svane, and
C. O. Rodriguez
- Electrical and magnetic properties of the two crystallographic forms of BaRuO_3 4561
J. T. Rijssenbeek, R. Jin, Yu. Zadorozhny, Y. Liu, B. Batlogg, and R. J. Cava
- Phase separation in models for correlated electrons 4565
Kristel Michielsen and Hans De Raedt

Semiconductors I: bulk

- Light-induced creation of metastable defects in hydrogenated amorphous silicon studied by computer simulations
of constant photocurrent measurements 4568
J. A. Schmidt, R. D. Arce, R. R. Koropecski, and R. H. Buitrago
- Deep-level-driven anomalous temperature dependence of lattice constants and energy gaps in $\text{Mg}_x\text{Zn}_{1-x}\text{Se}$ and
 $\text{Mg}_x\text{Zn}_{1-x}\text{Se}:\text{Co}^{2+}$ single crystals 4572
Wha-Tek Kim
- Temperature-dependent electron-lattice thermalization in GaAs 4576
N. Del Fatti, P. Langot, R. Tommasi, and F. Vallée

Semiconductors II: surfaces, interfaces, microstructures, and related topics

- Two-dimensional hopping conductivity in a δ -doped $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ heterostructure 4580
S. I. Khondaker, I. S. Shlimak, J. T. Nicholls, M. Pepper, and D. A. Ritchie
- Mixed biexcitons in single quantum wells 4584
H. P. Wagner, W. Langbein, and J. M. Hvam



Atomic structure of the Sb-induced Si(111)-(5 $\sqrt{3}\times 5\sqrt{3}$)R30° surface: <i>Ab initio</i> calculations	4588
Young-Jo Ko, Kang-Ho Park, Jeong Sook Ha, and Wan Soo Yun	
Evolution of macrosteps on 6H-SiC(0001): Impurity-induced morphological instability of step trains	4592
Noboru Ohtani, Masakazu Katsuno, Jun Takahashi, Hirokatsu Yashiro, and Masatoshi Kanaya	
Effects of diffusional anisotropy and substrate inhomogeneity on length-distribution scaling of dimerized chains	4596
J. L. Iguain, H. O. Martín, and C. M. Aldao	
Optical properties of anisotropic exciton: Hyperspherical theory	4600
E. A. Muljarov, A. L. Yablonskii, S. G. Tikhodeev, A. E. Bulatov, and Joseph L. Birman	
Spin-density-functional theory of circular and elliptical quantum dots	4604
Kenji Hirose and Ned S. Wingreen	
Coherent transport through a quantum dot embedded in an Aharonov-Bohm ring	4608
Kicheon Kang	
Bound states revealed by time-periodic perturbing scattering potentials	4612
G. Burmeister and K. Maschke	
Phase coherence in mesoscopic systems at low temperatures	4615
Kamran Houshangpour and Klaus Maschke	
Temperature-dependent studies of InAs base layers for ballistic electron emission microscopy	4618
R. Heer, J. Smoliner, G. Strasser, and E. Gornik	
Evidence for ballistic electron transport exceeding 160 μm in an undoped GaAs/Al _x Ga _{1-x} As field-effect transistor	4622
G. R. Facer, B. E. Kane, A. S. Dzurak, R. J. Heron, N. E. Lumpkin, R. G. Clark, L. N. Pfeiffer, and K. W. West	
Image-soliton method applied to finite multiple tunnel junctions	4626
M. B. A. Jalil and M. Wagner	
Carrier capture and escape in In _x Ga _{1-x} As/GaAs quantum dots: Effects of intermixing	4630
S. Marcinkevičius and R. Leon	
Band-edge modifications due to photogenerated carriers in single <i>p</i> -type δ -doped GaAs layers	4634
A. Levine, E. C. F. da Silva, G. M. Sipahi, A. A. Quivy, L. M. R. Scolfaro, J. R. Leite, I. F. L. Dias, E. Lauretto, J. B. B. de Oliveira, E. A. Meneses, and A. G. Oliveira	
Validity of the Kardar-Parisi-Zhang equation in the asymptotic limit of metal electrodeposition	4638
P. L. Schilardi, O. Azzaroni, R. C. Salvarezza, and A. J. Arvia	
Surface physics, low-dimensional systems, and related topics	
Iterative method of calculating reflection-high-energy-electron-diffraction intensities	4642
Z. Mitura	
Direct atomistic observation of deformation in multiwalled carbon nanotubes	4646
Tokushi Kizuka	
Evolution of surface morphology during Fe/Si(111) and Fe/Si(001) heteroepitaxy	4650
H. J. Kim, D. Y. Noh, J. H. Je, and Y. Hwu	
Scanned potential microscopy of edge and bulk currents in the quantum Hall regime	4654
Kent L. McCormick, Michael T. Woodside, Mike Huang, Mingshaw Wu, Paul L. McEuen, Cem Duruoğlu, and J. S. Harris, Jr.	
Time-dependent single molecule spectral lines	4658
Taras Plakhotnik	

ARTICLES

Electronic structure: wide-band, narrow-band, and strongly correlated systems

Polarized ultraviolet absorption of highly oriented poly(2-methoxy, 5-(2'-ethyl)-hexyloxy) paraphenylene vinylene	4661
E. K. Miller, D. Yoshida, C. Y. Yang, and A. J. Heeger	
Possible exotic phases in the one-dimensional extended Hubbard model	4665
R. Torsten Clay, Anders W. Sandvik, and David K. Campbell	
Band widening in graphite	4680
C. Heske, R. Treusch, F. J. Himpsel, S. Kakar, L. J. Terminello, H. J. Weyer, and E. L. Shirley	
Extrapolative approaches to Brillouin-zone integration	4685
C. J. Pickard and M. C. Payne	
Correlated optimized effective-potential treatment of the derivative discontinuity and of the highest occupied Kohn-Sham eigenvalue: A Janak-type theorem for the optimized effective-potential model	4694
Mark E. Casida	
Magnetic anisotropy in density-functional theory	4699
H. J. F. Jansen	
Unified treatment of asymptotic van der Waals forces	4708
Erika Hult, Henrik Rydberg, Bengt I. Lundqvist, and David C. Langreth	
Effect of quasi-two-dimensional Fermi surfaces on electronic properties in YbSb ₂	4714
N. Sato, T. Kinokiri, T. Komatsubara, and H. Harima	
Fermi surface of the ferromagnetic semimetal, EuB ₆	4720
M. C. Aronson, J. L. Sarrao, Z. Fisk, M. Whittton, and B. L. Brandt	
Crystal-orientation effects on the piezoelectric field and electronic properties of strained wurtzite semiconductors ..	4725
Seoung-Hwan Park and Shun-Lien Chuang	
Ground-state phase diagram of the one-dimensional dimerized t - J model at quarter filling	4738
S. Nishimoto and Y. Ohta	
Hall effect in the perovskite manganites	4746
Pinaki Majumdar, Steven H. Simon, and Anirvan M. Sengupta	
Variable-range hopping: Role of Coulomb interactions	4752
Subhalakshmi Lamba and Deepak Kumar	
Dielectric properties of the electron glass	4766
Subhalakshmi Lamba and Deepak Kumar	
Model of semimetallic behavior in strongly correlated electron systems	4777
Stefan Blawid	
Photoconversion of F -type centers in thermochemically reduced MgO single crystals	4786
R. González, M. A. Monge, J. E. Muñoz Santistue, R. Pareja, Y. Chen, E. Kotomin, M. M. Kukla, and A. I. Popov	
Valence-band electronic structure of Co ₃ O ₄ epitaxy on CoO(100)	4791
M. A. Langell, M. D. Anderson, G. A. Carson, L. Peng, and S. Smith	
Exploring level statistics from quantum chaos to localization with the autocorrelation function of spectral determinants	4799
Stefan Kettemann	
Staggered-spin contribution to nuclear spin-lattice relaxation in two-leg antiferromagnetic spin- $\frac{1}{2}$ ladders	4803
D. A. Ivanov and Patrick A. Lee	

Semiconductors I: bulk

Local atomic structure of semiconductor alloys using pair distribution functions. II.	4807
Jean S. Chung and M. F. Thorpe	
Chemical and strain effects on Boron-doped Si(100)	4813
M. Ramamoorthy, E. L. Briggs, and J. Bernholc	
Diagrammatic exciton-basis valence-bond theory of linear polyenes	4822
M. Chandross, Y. Shimoi, and S. Mazumdar	
Theory of even-parity states in polyphenylenes	4839
A. Chakrabarti and S. Mazumdar	
Electron-spin-resonance center of dangling bonds in undoped α -Si:H	4849
T. Umeda, S. Yamasaki, J. Isoya, and K. Tanaka	
Excitation spectrum of a PtLi-related center in silicon	4858
Per Tidlund, Mats Kleverman, and Pavel Hazdra	
Amphoteric charge states and diffusion barriers of hydrogen in GaAs	4864
C. Wang and Q.-M. Zhang	
Hydrogen-induced states near the GaAs band edges	4869
A. Amore Bonapasta, Mario Capizzi, and Paolo Giannozzi	
Energy levels of the d^8 electron and d^2 hole system	4881
Du Mao Lu and Tae Ho Yeom	
Dynamics of coherent hole-population transfer between valence subbands in diamond- and zinc-blende-type semiconductors	4888
A. Dargys	
Numerical calculation of relaxation rates in amorphous silicon	4894
S. R. Bickham	
Mechanism for hydrogen-enhanced oxygen diffusion in silicon	4898
R. B. Capaz, L. V. C. Assali, L. C. Kimerling, K. Cho, and J. D. Joannopoulos	
Master-equation approach to the study of electronic transport in small semiconductor devices	4901
M. V. Fischetti	
Dynamics of negative muonium in n -type silicon	4918
B. Hitti, S. R. Kreitzman, T. L. Estle, E. S. Bates, M. R. Dawdy, T. L. Head, and R. L. Lichti	

Semiconductors II: surfaces, interfaces, microstructures, and related topics

Atomic geometry, electronic structure, and vibrational properties of the AlSb(110) and GaSb(110) surfaces	4925
H. M. Tütüncü and G. P. Srivastava	
Scattering of vibrational waves in perturbed two-dimensional multichannel asymmetric waveguides as on an isolated step	4933
A. Virlouvet, A. Khater, H. Aouchiche, O. Rafil, and K. Maschke	
Ultrafast carrier dynamics near the Si(100)2 $\times$ 1 surface	4943
Seongtae Jeong and Jeffrey Bokor	
Hubbard-gap tunneling in disordered quantum-dot chains	4952
Ryuichi Ugajin	
Localized electronic states of a terminated superlattice with a δ defect in the subsurface region	4961
A. Kaczyński, R. Kucharczyk, and M. Stęślicka	
Magnetotransport theory in quantum dots: 3D-0D and 2D-0D tunneling and angular momentum selection rules ...	4966
B. Jouault, M. Boero, G. Faini, and J. C. Inkson	
Dynamics of exciton localization in CdS/HgS quantum-dot quantum wells	4973
Alvin T. Yeh, Giulio Cerullo, Uri Banin, Alf Mews, A. Paul Alivisatos, and Charles V. Shank	

Confinement and electron-phonon interactions of the E_1 exciton in self-organized Ge quantum dots	4980
S. H. Kwok, P. Y. Yu, C. H. Tung, Y. H. Zhang, M. F. Li, C. S. Peng, and J. M. Zhou	
Effects of resonant tunneling on magnetoresistance through a quantum dot	4985
Tetsufumi Tanamoto and Shinobu Fujita	
Quantum energy flow in mesoscopic dielectric structures	4992
M. P. Blencowe	
Transverse magnetoresistance of the two-dimensional chiral metal	4999
J. T. Chalker and S. L. Sondhi	
Unoccupied band structure of wurtzite GaN(0001)	5003
T. Valla, P. D. Johnson, S. S. Dhesi, K. E. Smith, D. Doppalapudi, T. D. Moustakas, and E. L. Shirley	
Luminescence and Raman scattering in periodically δ -doped GaAs	5008
C. A. Siqueira, W. N. Rodrigues, M. V. B. Moreira, A. G. de Oliveira, A. S. Chaves, and L. Ioriatti	
Dispersion of polar optical phonons in wurtzite quantum wells	5013
S. M. Komirenko, K. W. Kim, M. A. Stroschio, and M. Dutta	
Time-resolved studies of single semiconductor quantum dots	5021
Valéry Zwiller, Mats-Erik Pistol, Dan Hessman, Rolf Cederström, Werner Seifert, and Lars Samuelson	
Time-resolved Fourier-transform infrared and visible luminescence spectroscopy of photoexcited porous silicon	5026
Jianping Wang, Li Song, Bingsuo Zou, and Mostafa A. El-Sayed	
Bose-Einstein statistics in thermalization and photoluminescence of quantum-well excitons	5032
A. L. Ivanov, P. B. Littlewood, and H. Haug	
Excitation intensity dependence of photoluminescence from narrow $\langle 100 \rangle$ - and $\langle 111 \rangle$ A-grown $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ single quantum wells	5049
T. Sauncy, M. Holtz, O. Brafman, D. Fekete, and Y. Finkelstein	
Photoluminescence studies of $\langle 100 \rangle$ and $\langle 111 \rangle$ $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ single quantum wells under hydrostatic pressure	5056
T. Sauncy, M. Holtz, O. Brafman, D. Fekete, and Y. Finkelstein	
Temperature dependence of the optical properties of $\text{InAs}/\text{Al}_y\text{Ga}_{1-y}\text{As}$ self-organized quantum dots	5064
A. Polimeni, A. Patanè, M. Henini, L. Eaves, and P. C. Main	
Phonon bottleneck in quantum dots: Role of lifetime of the confined optical phonons	5069
Xin-Qi Li, Hajime Nakayama, and Yasuhiko Arakawa	
Interfacial stability and atomistic processes in the $a\text{-C}/\text{Si}(100)$ heterostructure system	5074
P. C. Kelires, M. Gioti, and S. Logothetidis	
Exciton-light coupling in single and coupled semiconductor microcavities: Polariton dispersion and polarization splitting	5082
Giovanna Panzarini, Lucio Claudio Andreani, A. Armitage, D. Baxter, M. S. Skolnick, V. N. Astratov, J. S. Roberts, Alexey V. Kavokin, Maria R. Vladimirova, and M. A. Kaliteevski	
Small- q anomaly in the dielectric function and high-temperature oscillations of the screening potential in a two-dimensional electron gas with spin-orbit coupling	5090
Guang-Hong Chen and M. E. Raikh	
High-depth-resolution Rutherford backscattering data and error analysis of SiGe systems using the simulated annealing and Markov chain Monte Carlo algorithms	5097
N. P. Barradas, A. P. Knights, C. Jeynes, O. A. Mironov, T. J. Grasby, and E. H. C. Parker	
Surface physics, low-dimensional systems, and related topics	
Electron inelastic mean free path, electron attenuation length, and low-energy electron-diffraction theory	5106
J. Rundgren	

Initial stages of Ba adsorption on the Si(100)-(2×1) surface at room temperature	5115
X. Yao, Xiaoming Hu, D. Sarid, Z. Yu, J. Wang, D. S. Marshall, R. Droopad, J. K. Abrokwhah, J. A. Hallmark, and W. J. Ooms	
Interpretation of long-range interatomic force	5120
A. Buldum, S. Ciraci, C. Y. Fong, and J. S. Nelson	
Tip-geometry effects in circularly polarized light emission from a scanning tunneling microscope	5126
Egidijus Anisimovas and Peter Johansson	
Detailed atomic structure of arbitrary fcc [100] twist grain boundaries	5134
D. Romeu, L. Beltrán-del-Rio, J. L. Aragón, and A. Gómez	
Density functional periodic study of CO adsorption on the Pd ₃ Mn(100) alloy surface: Comparison with Pd(100)	5142
F. Delbecq and P. Sautet	
Dynamical transitions and sliding friction in the two-dimensional Frenkel-Kontorova model	5154
Enzo Granato and S. C. Ying	
Role of nitrogen in the formation of hard and elastic CN _x thin films by reactive magnetron sputtering	5162
Niklas Hellgren, Mats P. Johansson, Esteban Broitman, Lars Hultman, and Jan-Eric Sundgren	
Photoemission intensity oscillations from quantum-well states in the Ag/V(100) overlayer system	5170
M. Milun, P. Pervan, B. Gumhalter, and D. P. Woodruff	
Interaction between oxygen vacancies on MgO(100)	5178
Fabio Finocchi, Jacek Goniakowski, and Claudine Noguera	
Resonant soft-x-ray emission spectroscopy of surface adsorbates: Theory, computations, and measurements of ethylene and benzene on Cu(110)	5189
Luciano Triguero, Yi Luo, Lars G. M. Pettersson, Hans Ågren, Peter Väterlein, Martin Weinelt, Alexander Föhlisch, Jörgen Hasselström, Olof Karis, and Anders Nilsson	
Metal oxide heteroepitaxy: Stranski-Krastanov growth for iron oxides on Pt(111)	5201
W. Weiss and M. Ritter	
Electronic structure and magnetism of Rh _n ($n=2-13$) clusters	5214
B. V. Reddy, S. K. Nayak, S. N. Khanna, B. K. Rao, and P. Jena	
Exact numerical study of the ground-state magnetic properties of clusters	5223
F. López-Urías and G. M. Pastor	
Electron spectroscopy on boron nitride thin films: Comparison of near-surface to bulk electronic properties	5233
P. Widmayer, H.-G. Boyen, P. Ziemann, P. Reinke, and P. Oelhafen	
Effects of magnetic field and disorder on the electronic properties of carbon nanotubes	5242
Stephan Roche and Riichiro Saito	
Evidence for $S=0$ -type spin pairing in the nonferromagnetic modification of TDAE-C ₆₀	5247
D. Arčon, R. Blinc, P. Cevc, and A. Omerzu	
Cumulative Author Index	5252